ABSTRACT

ETCHING SOLUTION FOR ETCHING POROUS SILICON, ETCHING METHOD USING THE ETCHING SOLUTION AND METHOD OF PREPARING SEMICONDUCTOR MEMBER USING THE ETCHING SOLUTION

A method for preparing a semiconductor member comprises:

forming a substrate having a non-porous silicon monocrystalline layer and a porous silicon layer;

bonding another substrate having a surface made of an insulating material to the surface of the monocrystalline layer; and

etching to remove the porous silicon layer by immersing in an etching solution.

FIGURE 10A TO 10C

This Sheet Has Been Replaced

